FIG. 1

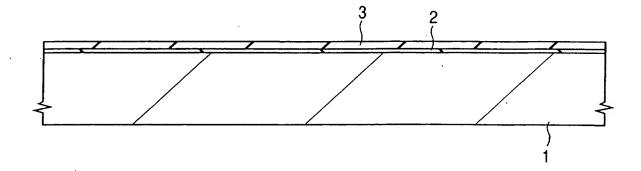


FIG. 2

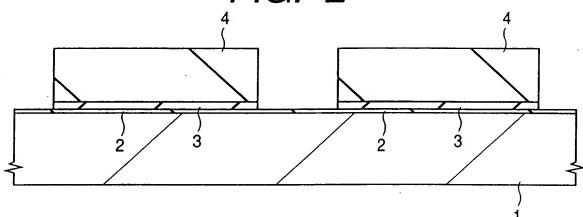
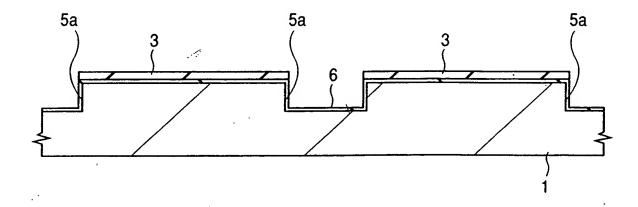


FIG. 3



0)

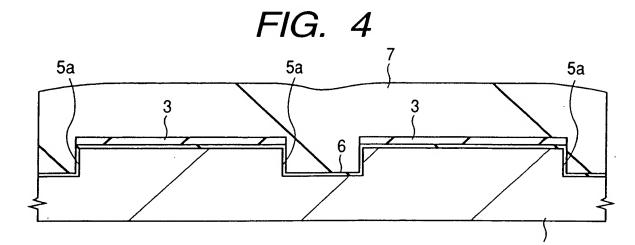


FIG. 5

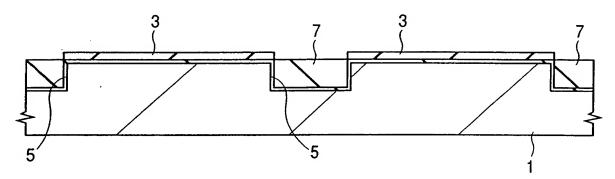


FIG. 6

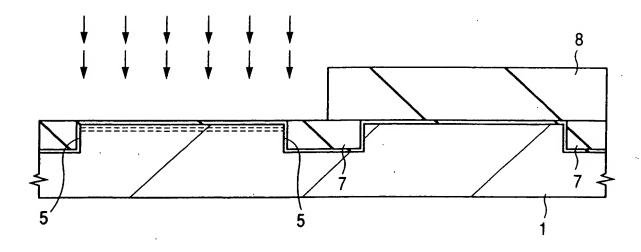


FIG. 7

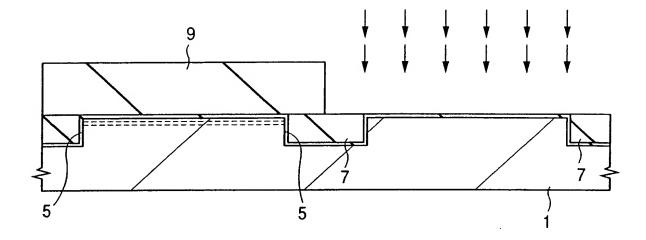


FIG. 8

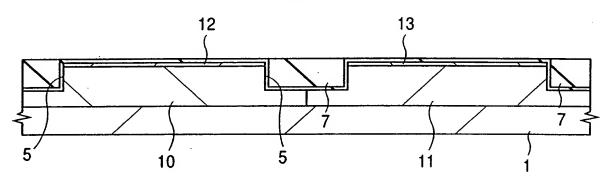
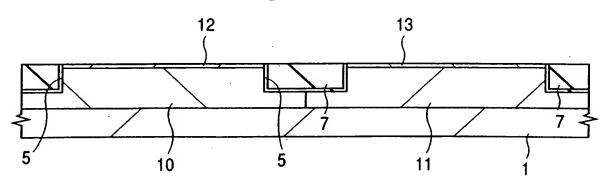
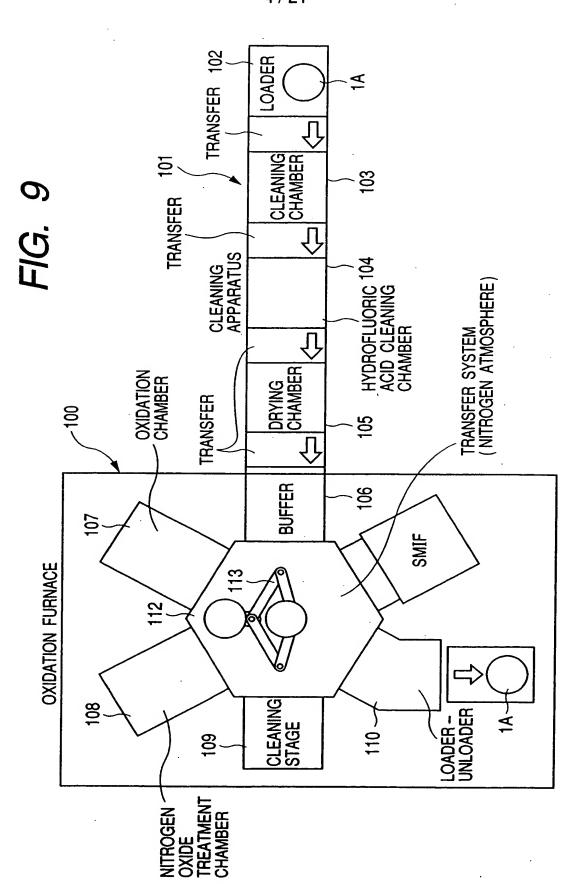


FIG. 10

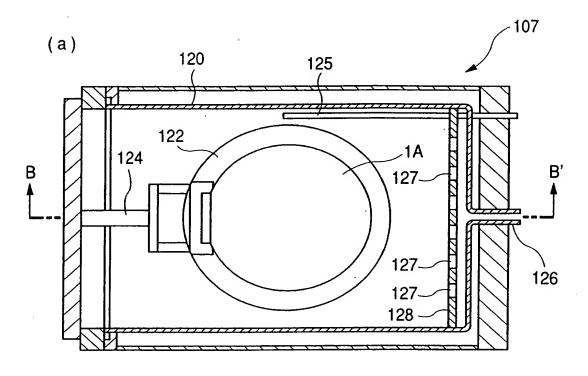


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FIG. 11



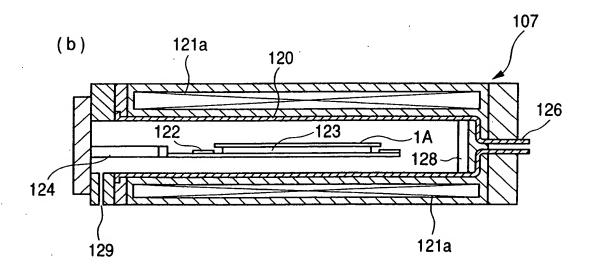
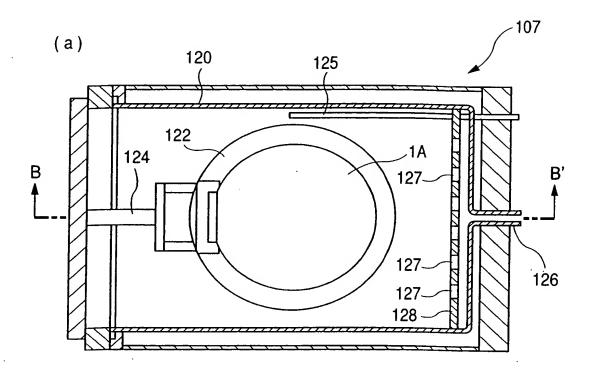
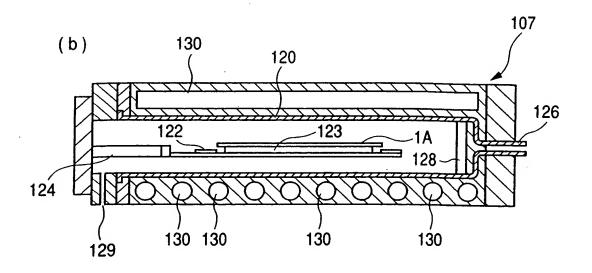
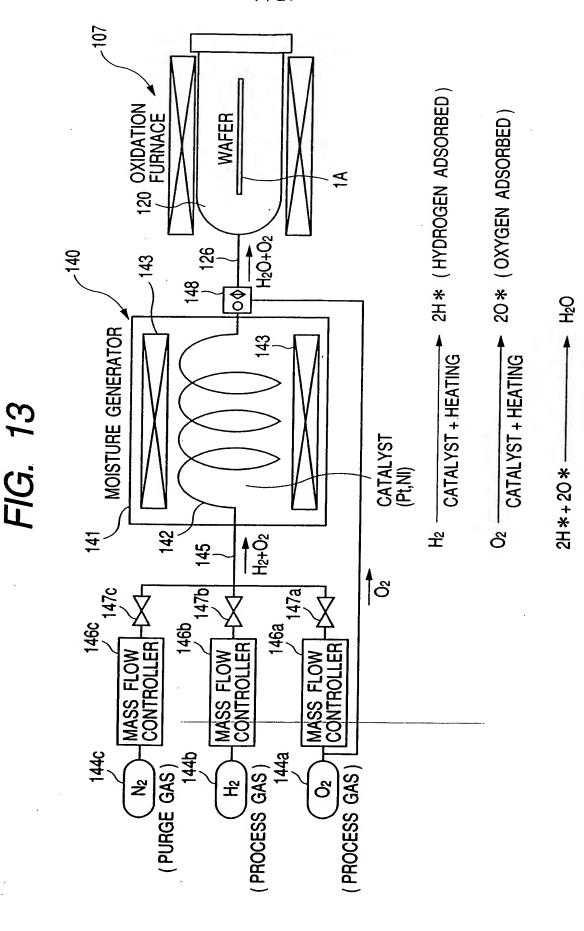


FIG. 12





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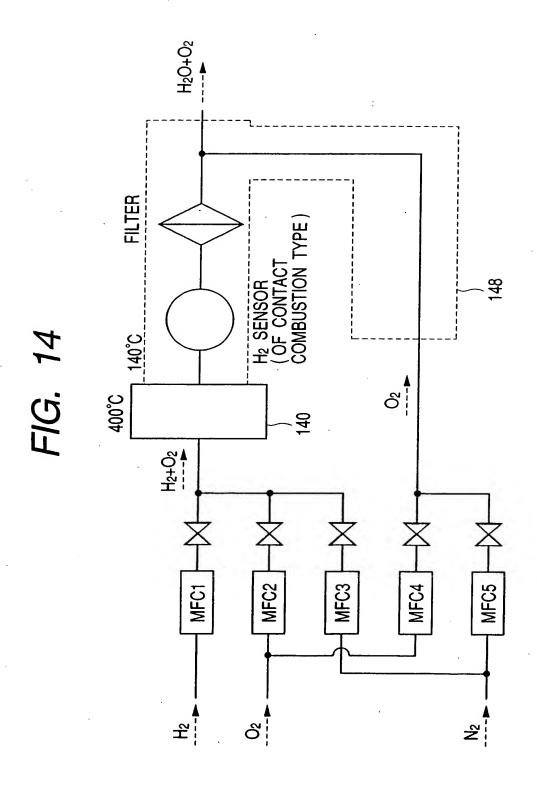


FIG. 15	WAFER					•					
	AFTER- PURGE	2' 20"									
	OXIDATION	ດ໌									
	H ₂ INTRODUCTION	15"									
	O ₂ PURGE	0 – 55"									
	N ₂ PURGE	1,									
	WAFER	.22,									
		TIME	N ₂ FLOW RATE		O ₂ FLOW RATE			H ₂ FLOW RATE			

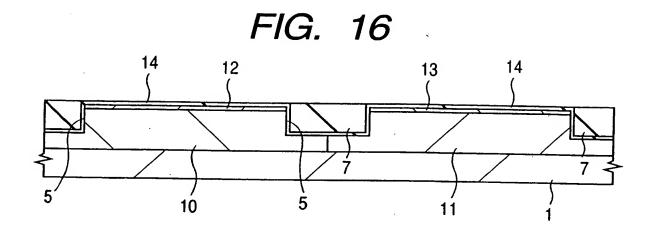


FIG. 17

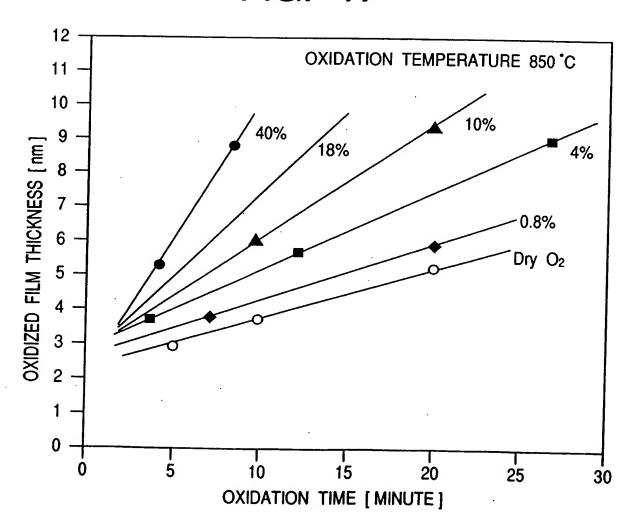
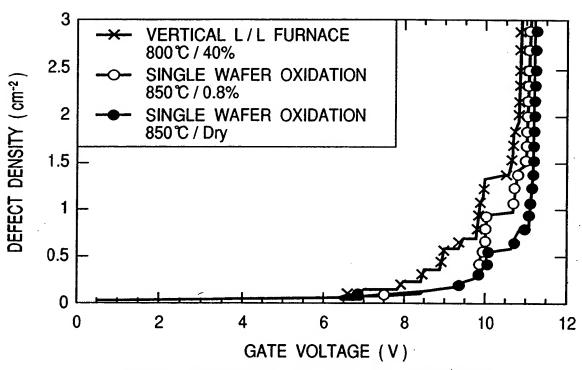


FIG. 18



INITIAL WITHSTAND VOLTAGE OF LOW MOISTURE CONTENT OXIDE FILM (OXIDE FILM THICKNESS = $9nm,S = 0.19cm^2$)

FIG. 19

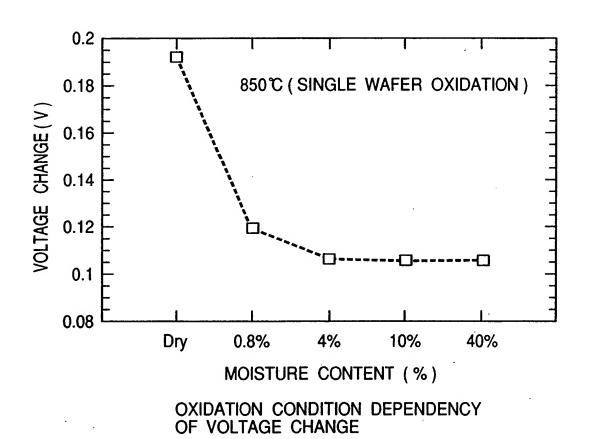
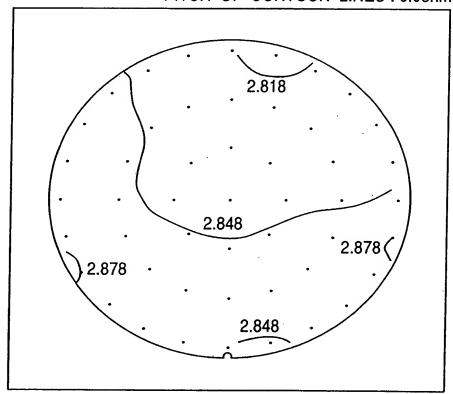


FIG. 20





WAFER DIAMETER: 8 inch

AVERAGE: 2.848 [nm]

MAX.: 2.881 [nm]

MIN.: 2.814 [nm]

MAX. - MIN.: 0.067 [nm]

±1.18[%]

TREATING CONDITIONS: 850°C, 2'30"

H₂ / O₂: 0.05 / 4.9slm (MOISTURE CONTENT: 0.8%)

MEASUREMENT: AT 49 POINTS BY ELLIPSOMETER

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FIG. 21

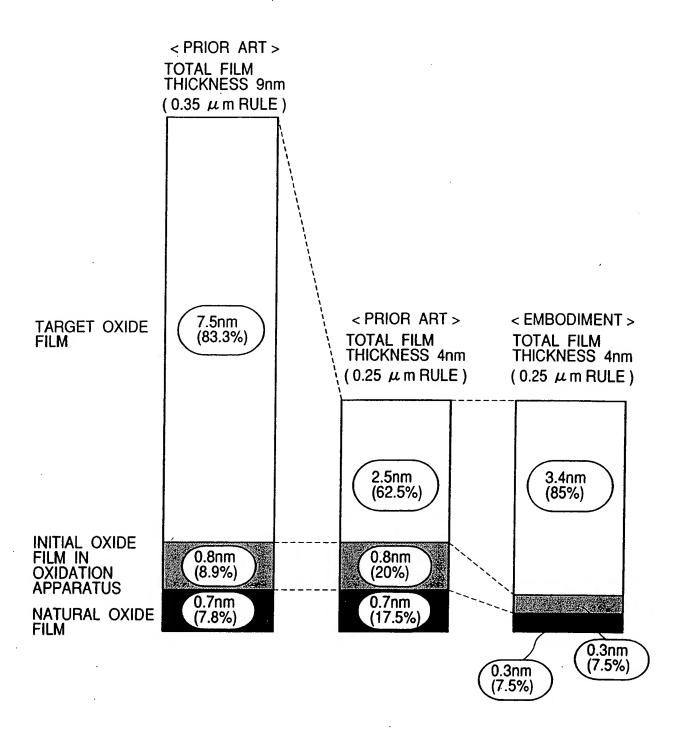


FIG. 22

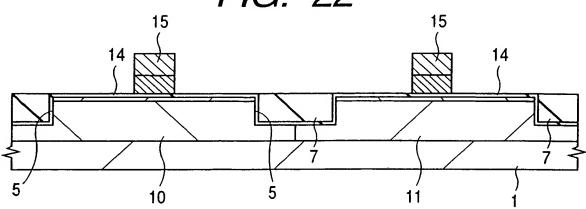


FIG. 23

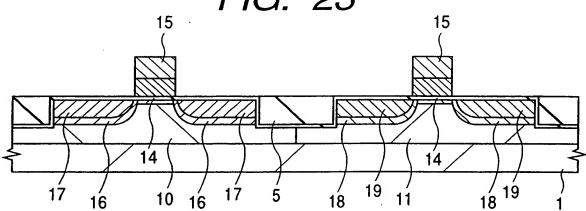


FIG. 24

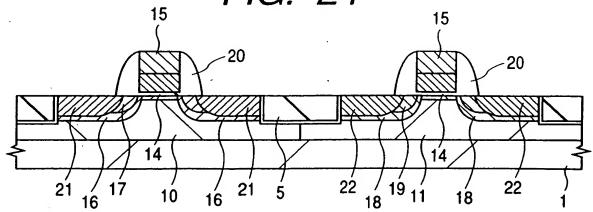


FIG. 25

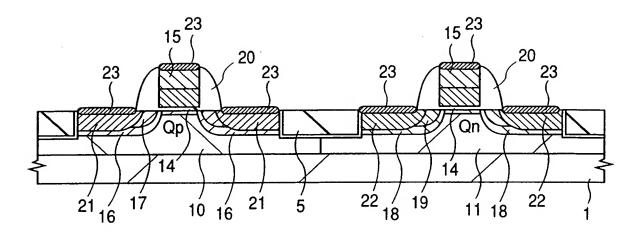


FIG. 26

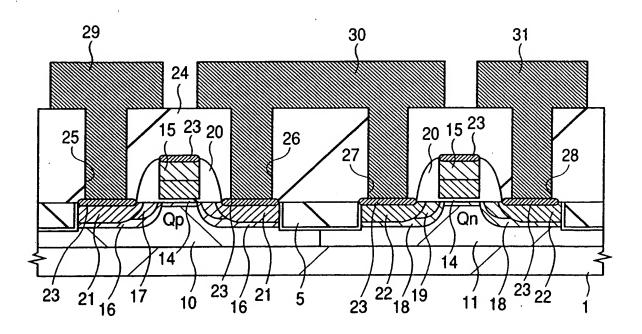


FIG. 27

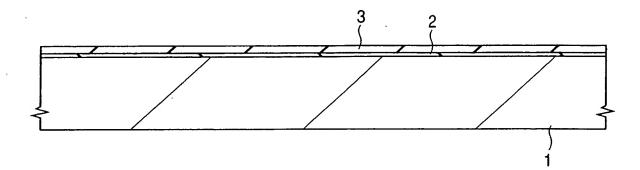


FIG. 28

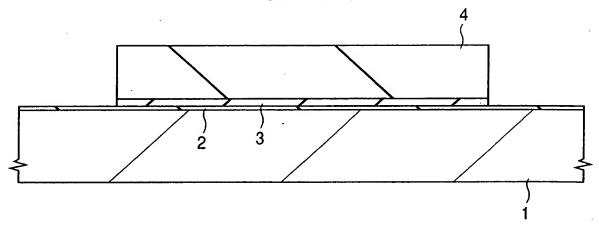


FIG. 29

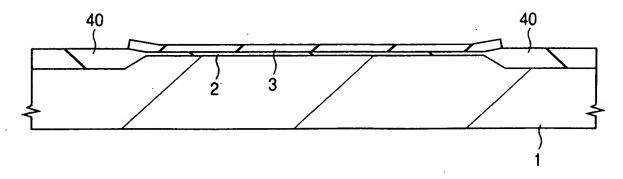
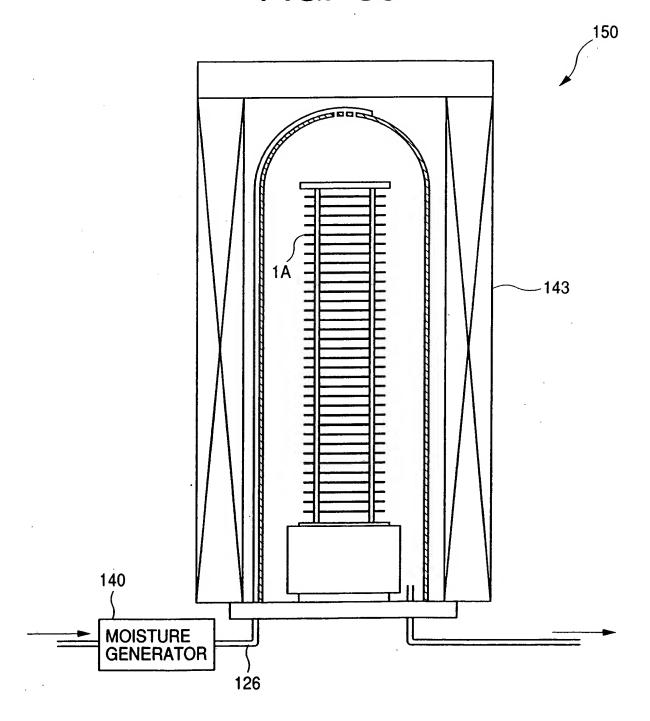


FIG. 30



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WAFER UNLOAD <u>.</u>0 AFTER-Purge 2, 20'' ARBITRARY (SEVERAL MINS.) OXIDATION FIG. 31 H₂ INTRODUCTION 5 o₂ Purge ີລ N₂ Purge WAFER LOAD **Q** TIME N₂ FLOW RATE O₂ FLOW RATE H₂ FLOW RATE

()()

FIG. 32

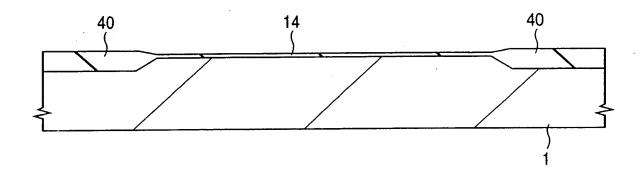
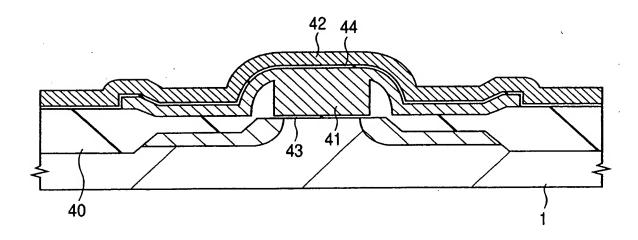


FIG. 34



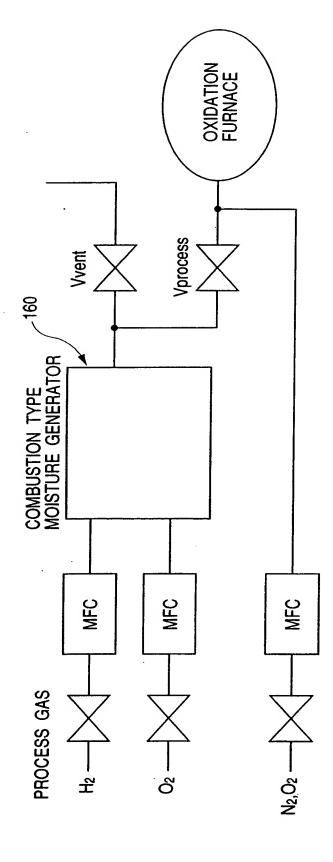


FIG. 33